

OCXO2525L-100MHz-D-V

Sinewave OCXO with Ultra-Low Phase Noise

Features and Benefits

Ultra-Low phase noise <-165 dBc/Hz @ 1KHz offset <-178 dBc/Hz @ 100KHz offset +11 dBm min output power Sine wave output 25.8 x 25.8 x 13.5 mm

Description

Cutting edge ultra-low noise SC-cut resonator technology utilized in low noise 100 MHz oscillator topology with proprietary impedance matching tuning algorithm.

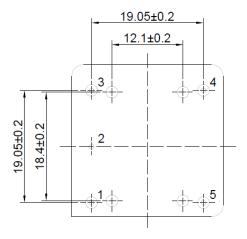
Typical Applications

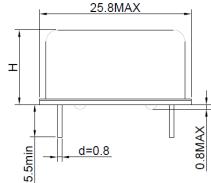
Customized Frequency source for Microwave Communications / Synthesizer Modules

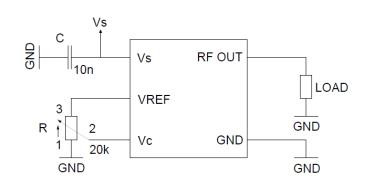
Mechanical Drawing & Pin Connections

Drawing No:

MD150074-1







Pin connections

PIN#	Symbol	Function
1	RF OUT	RF Output
2	GND	Ground
3	Vc	Control Voltage(EFC)
4	VREF	Reference Voltage
5	Vs	Supply Voltage

Unit = mm 1mm=0.0394inch

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Specifications

Davamatar	Condition		1114		
Parameter	Condition	Min.	Тур.	Max.	Unit
Frequency Range		80		125	MHz
Standard Frequencies		100.000			MHz
RF Output					
Output Waveform		Sine wave			
Load R _L	±5%		50		Ω
Output Level (Note 2)		+11			dBm
Harmonics				-30	dBc
Spurious				-90	dBc
Warm-up time	$\Delta f_{\text{final}}/f_0 < \pm 0.1 \text{ppm}$		3	5	min
G-Sensitivity	Per axis			1.0	ppb/g
Voltage and Power Consumption					
Reference Voltage VREF Output (Note 3)			10.0		V
Supply Voltage V _S (Note 3)		11.4	12.0	12.6	V
	Warm-up (Note 4)			350	mA
Current Consumption	Steady-state			150	A
·	@ +25°C (Note 4)			150	mA
Frequency Adjustment Range	· · · · · · · · · · · · · · · · · · ·				
Electronic Frequency Control (EFC)		±1	±2		ppm
EFC Voltage V _C		0	VREF/2	VREF	V
EFC Slope (Δf/ΔV _C)	Positive				
EFC Input Impedance		100			ΚΩ
Frequency Stability					
Initial Tolerance @+25°C	V _C @ VREF / 2			±300	ppb
Vs. Operating Temperature Range	Steady state	Please refer to the options tables below		· -	
Vs. Supply Voltage Variations (pushing)	Vs ±5%			±10	ppb
Vs. Load Change (pulling)	R _L ±5%			±5	ppb
<u> </u>	After 30days		4		•
Long Term Aging Per Day	operation		±1	±2	ppb
Land Tarre Asian First Van	After 30days		400	000	
Long Term Aging First Year	operation		±100	±200	ppb
Phase Noise	·				
1KHz	<-165				dBc/Hz
100KHz	<-178				
Size, Weight and Packaging					
Size	25.8 x 25.8 x 13.5mm	Max. IEC 6	0679-3 CO43	3	
Weight	20g				
Packaging	Palette				
	1				

Notes:

- 1. Terminology and test conditions are according to IEC60679-1 and MIL-PRF-55310, unless otherwise stated
- 2. Other output level on request
- 3. Other supply and reference voltage available on request
- 4. Maybe higher for wide operating temperature range

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Absolute Maximum Ratings

Parameter	Condition	Va	Unit		
Farailletei	Condition	Min.	Max.	Unit	
Supply Voltage V _S	V _S to GND	-0.5	V _S + 10%	V	
Control Voltage V _C	V_C to GND	-0.5	15	V	
Storage Temperature		-55	+125	°C	

Ordering Options Codes

Stability vs. Temperature

Table 1				
Freq	uency Stability			
Code	Stability in ppb			
1	±5			
2	±10			
3	±25			
4	±50			
5	±100			
6	±200			

Table 2					
Lower Ter	Lower Temperature				
Code	ů				
1	0				
2	-10				
3	-20				
4	-30				
5	-40				
6	-55				

Table 3				
Upper Te	mperature			
Code	°C			
1	+50			
2	+60			
3	+70			
4	+75			
5	+80			
6	+85			

	Temperature Code and Range °C							
Frequency Stability	Code	11	22	33	43	54	56	66
Code	Temperature	0 ~ +50	-10 ~ +60	-20 ~ +70	-30 ~ +70	-40 ~ +75	-40 ~ +85	-55 ~ +85
		Available	Available	Available	Available	Not	Not	Not
1		On	On	On	On	Available	Available	Available
		Request	Request	Request	Request			
					Available	Available	Not	Not
2		Available	Available	Available	On	On	Available	Available
					Request	Request		
							Available	Available
3		Available	Available	Available	Available	Available	On	On
							Request	Request
4		Available						
5		Available						
6		Available						

Ordering Code

Model	Stability	Temperature
OCXO2525L-100MHz	Table 1	Table 2 & 3

Example

OCXO2525L-100MHz-D-V-4-33 denotes

OCXO2525L in 100MHz with ±50ppb stability and temperature range of -20 ~ +70°C

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Testing

Parameter	Procedu	re	Condition
Electrostatic Discharge (ESD)			
THD Devices	IEC60749-26	HBM	2000V
SMD Devices	IEC60749-27	MM	200V
Washable	Yes		
RoHS-Compliant	Yes		

Performance Graph section



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Environmental Conditions

Test	IEC 60068 Part	OEC60679-1 Clause	MIL-STD- 202G Method	MIL-STD- 810F Method	Mil-PRF- 55310D Clause	Test Conditions (IEC)
Sealing Tests (if applicable)	2-17	5.6.2	112E		3.6.1.2	Gross leak: Test Qc Fine leak: Test Qk
Solderability Resistance to Soldering Heat	2-20 2-58	5.6.3	208H 210F		3.6.52 3.6.48	Test Ta Method 1 Test Td ₁ Method 2 Test Td ₂ Method 2
Shock	2-27	5.6.8	213B	516.4	3.6.40	Test Ea, 3 x per axes 100g, 6ms half-sine pulse
Vibration, Sinusoidal*	2-6	5.6.7.1	201A 204D	516.4-4	3.6.38.1 3.6.38.2	Test F _C , 30 min per axes 10 Hz – 55 Hz 0,75mm; 55Hz – 2 kHz, 10g
Vibration, Random	2-64	5.6.7.3	214A	514.5	3.6.38.3 3.6.38.4	Test Fdb
Endurance Tests - Aging - Extended aging		5.7.1 5.7.2	108A		4.8.35	30 days @ 85°C, OCXO @ 25°C 1000h, 2000h, 8000h @85°C

Other environment conditions available on request

Datasheet is for reference purpose only and maybe changed without notice.